

This listing of claims will replace all prior versions of claims in the application.

Claims 1-40. (cancelled)

Claim 41. (previously presented) A chemically-amplified positive tone photoresist,
the photoresist comprising a resin, a photoacid-generating compound and an amine other than a trialkylamine.

Claim 42. (previously presented) The photoresist of claim 41 wherein the amine is an aryl amine.

Claim 43. (previously presented) The photoresist of claim 41 wherein the amine is a cyclic amine.

Claim 44. (previously presented) The photoresist of claim 41 wherein the photoacid-generating compound is an iodonium compound.

Claim 45. (previously presented) The photoresist of claim 41 wherein the photoacid-generating compound is an aromatic sulfonium compound.

Claim 46. (previously presented) The photoresist of claim 41 wherein the resin is a phenol-based polymer.

Claim 47. (previously presented) An article of manufacture comprising a wafer substrate having coated thereon a photoresist of claim 41.

Claim 48. (currently amended) A method for forming a photoresist image on a wafer substrate for the production of a microprocessor, comprising:

- (a) providing a chemically-amplified positive tone photoresist, the photoresist comprising i) a resin, ii) a photoacid-generating compound and iii) a compound that comprises one or more moieties selected from ether, ester and amide;
- (b) forming a layer of a photoresist composition on the wafer substrate and exposing the photoresist layer to an image pattern of activating radiation; and
- (c) developing the exposed photoresist layer to form a photoresist relief image.

Claim 49. (previously presented) The method of claim 48 wherein the compound iii) comprises one or more ether moieties.

Claim 50. (previously presented) The method of claim 48 wherein the compound iii) comprises one or more ester moieties.

Claim 51. (previously presented) The method of claim 48 wherein the compound iii) comprises one or more amide moieties.

Claim 52. (previously presented) The method of claim 48 wherein the photoacid-generating compound is an iodonium compound.

Claim 53. (previously presented) The method of claim 48 wherein the photoacid-generating compound is an aromatic sulfonium compound.

Claim 54. (previously presented) The method of claim 48 wherein substrate areas bared of the photorsist layer upon development are selectively processed.

Claim 55. (previously presented) The method of claim 48 wherein substrate areas bared of the photorsist layer upon development are chemically etched.

Claim 56. (previously presented) The method of claim 48 wherein substrate areas bared of the photoresist layer upon development are plated.

Claim 57. (previously presented) The method of claim 48 wherein the resin is a phenol-based polymer.